

REPLACEMENT CLAIMS

Cancel claims 4 and 22-33 without prejudice.

Please use the following claims to replace those of the same number:

1 (Amended). An electronic component comprising:
a substrate; and
an airbridge located over the substrate and having at least a first layer and a second layer,
wherein a first portion of the second layer is over the first layer,
wherein:
a gap exists between a portion of the airbridge and the substrate; and
a thickness of the second layer is less than a combined thickness of the first layer
and the gap;
the airbridge is electrically conductive; and
the first layer of the airbridge is less resistive than the second layer of the
airbridge.

6 (Amended). The electronic component of claim 1 wherein:
a second portion of the second layer is located underneath an edge of the first layer.

14 (Amended) A semiconductor component comprising:
a semiconductor substrate;
a semiconductor device supported by the semiconductor substrate;
a first electrically insulative layer overlying the semiconductor substrate and the
semiconductor device; and
an airbridge located over the semiconductor substrate, located over the first electrically
insulative layer, and electrically coupled to the semiconductor device,
wherein:
a gap exists between a portion of the airbridge and the first electrically insulative
layer;
the airbridge has a first electrically conductive layer; and
the airbridge has a second electrically insulative layer overlying the first
electrically conductive layer.

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15 (Amended) The semiconductor component of claim 14 wherein:
the second electrically insulative layer is a passivation layer harder than the first electrically conductive layer; and
the airbridge further comprises:
an electrically conductive barrier layer located underneath the first electrically conductive layer and more resistive than the first electrically conductive layer.

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20 (Amended). A method of manufacturing an electronic component comprising:
providing a substrate;
forming an electrically insulative layer over the substrate;
forming a first layer over the first electrically insulative layer to form a first portion of an airbridge;
forming a first portion of a second layer over the first layer to form a second portion of the airbridge over the substrate,
wherein:
the airbridge is electrically conductive; and
the first layer of the airbridge is less resistive than the second layer of the airbridge; and
forming a gap between the airbridge and the electrically insulative layer.

21 (Amended). The method of claim 20 further comprising:
forming a semiconductor device at least partially located within the substrate; and
wherein:
forming the first layer further comprises:
providing the first layer comprised of an electrically conductive material;
forming the second layer further comprises:
providing the second layer comprised of an electrically insulative material;
and
forming the electrically insulative layer further comprises:
forming the electrically insulative layer over the semiconductor device.

34 (Amended). The method of claim 20 further comprising:
designing the airbridge to have a design width,
wherein:

forming the first layer further comprises:

forming the first layer to have a first layer width greater than the design
width; and

forming the second layer further comprises:

forming a second portion of the second layer underneath edges of the first
layer; and

keeping the second layer absent underneath a central portion of the first
layer, the central portion of the first layer having the design width.
